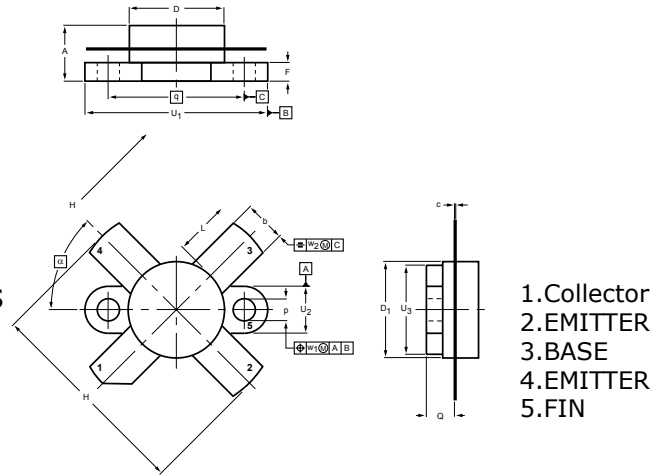


DESCRIPTION

Designed primarily for high-voltage applications as a high-power linear amplifier from 2.0 to 30 MHz.

FEATURES

- Specified 50V, 30MHz Characteristics
- $P_o = 150W$
- $G_p = 14$ dB min. at 150 W/30 MHz
- Omnigold™ Metalization System



DIMENSIONS

NOTE: ALL ELECTRODES ARE ISOLATED FROM FLANGE.

UNIT	A	b	c	D	D ₁	F	H	L	p	Q	q	U ₁	U ₂	U ₃	w ₁	w ₂	α
mm	7.27	5.82	0.16	12.86	12.83	2.67	28.45	7.93	3.30	4.45	18.42	24.90	6.48	12.32	0.51	1.02	45°
	6.17	5.56	0.10	12.59	12.57	2.41	25.52	6.32	3.05	3.91		24.63	6.22	12.06			
inches	0.286	0.229	0.006	0.506	0.505	0.105	1.120	0.312	0.130	0.175	0.725	0.98	0.255	0.485	0.02	0.04	
	0.243	0.219	0.004	0.496	0.495	0.095	1.005	0.249	0.120	0.154		0.97	0.245	0.475			

MAXIMUM RATINGS

CHARACTERISTICS	SYMBOL	RATINGS	UNITS
Collector-Base Voltage	V_{CB0}	175	V
Collector-Emitter Voltage	V_{CES}	175	V
Collector-Emitter Voltage	V_{CEO}	60	V
Collector Current	I_C	10	A
Emitter-Base Voltage	V_{EBO}	4	V
Collector Power Dissipation	P_{DISS}	240	W
Junction Temperature	T_J	-65 to 175	°C
Storage Temperature Range	T_{STG}	-65 to 175	°C

ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX	UNITS
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=100mA, I_B=0$	175	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C=100mA, V_{EB}=0$	175	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10mA, I_C=0$	4	-	-	V
Collector Cutoff Current	I_{CBO}	$(V_{CB} = 50 V, I_E = 0)$			5	mA
DC Current Gain	h_{FE}	$V_{CE}=6V, I_C=1.4A$	10	30	80	
Collector Output Capacitance	C_{ob}	$V_{CB}=50V, I_E=0$ $f=1MHz$	-	-	220	pF
Power Gain	G_p	$V_{CC}=50V, P_{OUT}=150$	14.0	-	-	dB
Collector Efficiency	η_C	$W, I_{CQ}=100mA$	40	-	-	%

Note : Above parameters , ratings , limits and conditions are subject to change.